## Hui Yang

## List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/3490510/publications.pdf

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		1937685	2053705	
5	48	4	5	
papers	citations	h-index	g-index	
5	5	5	36	
all docs	docs citations	times ranked	citing authors	

#	Article	IF	CITATIONS
1	Enhancement-mode thin film transistor using amorphous phosphorus-doped Indium–Zinc–Tin-Oxide channel layer. Materials Science in Semiconductor Processing, 2022, 137, 106228.	4.0	7
2	Influence of oxygen flow during sputtering process on the electrical properties of Ga-doped InZnSnO thin film transistor. Semiconductor Science and Technology, 2021, 36, 045006.	2.0	5
3	Annealing atmosphere-dependent electrical characteristics and bias stability of N-doped InZnSnO thin film transistors. Materials Science in Semiconductor Processing, 2020, 113, 105040.	4.0	12
4	Annealing temperature effects on the structural and electrical properties of N-doped In-Zn-Sn-O thin film transistors. Journal of Alloys and Compounds, 2019, 801, 33-39.	5 <b>.</b> 5	13
5	Preparation and electrical characteristics of N-doped In-Zn-Sn-O thin film transistors by radio frequency magnetron sputtering. Journal of Alloys and Compounds, 2018, 750, 1003-1006.	5.5	11